Solar Cells Optical Property - Photoconductivity



Sample: Solar Cell

Image Conditions: Contact Mode AFM Tr-IAFM Force (?? nN) Scan Speed (?? Hz)

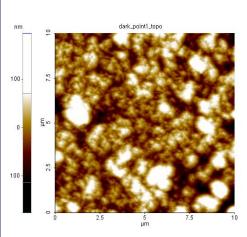
System Requirement: Closed-loop AFM System, Conductive AFM

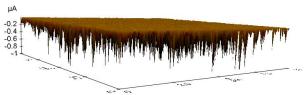
The Benefits

XE-AFM series offers many modes that are well suited for phtoonic devices and materials. In particular, Time Resolved Conductive AFM (Tr-IAFM) offers the ability to obtain the conductivity data with the AFM laser turned off (at alternative scan lines) so time resolved photo-induced current can be measured:

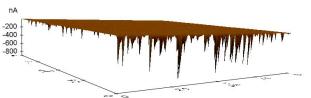
- a) with topography
- b) with nanoscale spatial resolution, and
- c) without interference from the AFM laser source.

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Topography (left image) and **photocurrent** (right images) with **laser source on** (top right image) and **laser source off** (bottom right image) show the effect of light in current generation; note the increased amount of photo-induced current in the upper image.



XE-Productivity in Action

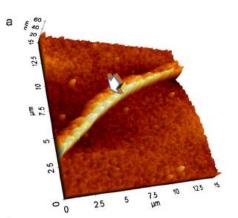
Jeongjin Lee, Inhee Choi, Surin Hong, SuSeung Lee, Young In Yang, Younghun Kim, Jongheop Yi; Construction of pcAFM module to measure photoconductance with a nanoscale spatial resolution; Ultramicroscopy 108 (2008) 1090–1093 Equipment: Park Systems XE-150

Abstract

A photoconductive atomic force microscopy (pcAFM) module was designed and the performance was tested. This module consisted of three units: the conductive mirror-plate, the steering mirror and the laser source. The module with a laser irradiation unit was equipped to a conventional conducting probe atomic force microscopy (CP-AFM) instrument to measure photoconductance in a nanoscale resolution. As a proof-of-concept experiment, the photoconductance of aggregated fullerene on indium tin oxide (ITO) substrate was measured with this module. The electrical signals (currents) of aggregated fullerene under the conditions of laser on/off at about -10V sample bias voltage were -100 to -160 nA and 0 to -20 nA, respectively. Results indicated that the pcAFM with this module allowed one to observe

photoinduced changes of electrical properties in

nanodevices with nanoscale spatial resolution.



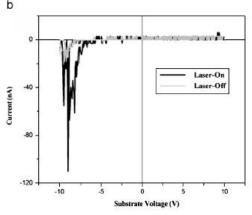


Fig. 3. (a) 3-D topography of the contact point for the I/I V curve measurement and (b) the measured I/I V curve. The resistance was decreased by a factor of 5-100. The arrow in (a) indicates the point at the slope of the sub-circle line, ca. 10 mm height from the bottom. At this point, the electrical signals (currents) of aggregated fullerene under the conditions of laser on/off at about -10 V sample bias voltage were -100 to -160 nA and 0 to -20 nA, respectively.